



# IMPORTANT NOTICE

10 December 2015

## 1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

In this document where the previous NXP references remain, please use the new links as shown below.

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Thank you for your cooperation and understanding,

WeEn Semiconductors

# DATA SHEET

## **BT258 series**

Thyristors  
logic level

Product specification

October 2002



# Thyristors

## logic level

## BT258 series

### GENERAL DESCRIPTION

Passivated, sensitive gate thyristors in a plastic envelope, intended for use in general purpose switching and phase control applications. These devices are intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

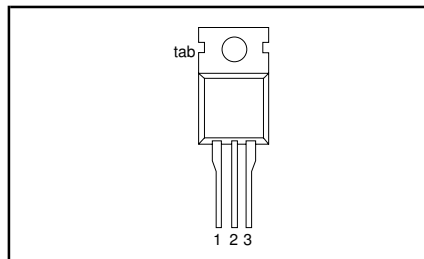
### QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	MAX.	MAX.	UNIT
$V_{DRM}$ , $V_{RRM}$	<b>BT258-</b> Repetitive peak off-state voltages	<b>500R</b> 500	<b>600R</b> 600	<b>800R</b> 800	V
$I_{T(AV)}$	Average on-state current	5	5	5	A
$I_{T(RMS)}$	RMS on-state current	8	8	8	A
$I_{TSM}$	Non-repetitive peak on-state current	75	75	75	A

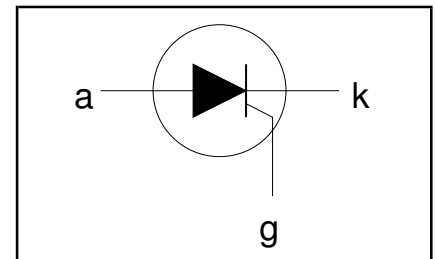
### PINNING - TO220AB

PIN	DESCRIPTION
1	cathode
2	anode
3	gate
tab	anode

### PIN CONFIGURATION



### SYMBOL



### LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.			UNIT
$V_{DRM}$ , $V_{RRM}$	Repetitive peak off-state voltages		-	<b>-500R</b> 500 <sup>1</sup>	<b>-600R</b> 600 <sup>1</sup>	<b>-800R</b> 800	V
$I_{T(AV)}$	Average on-state current	half sine wave; $T_{mb} \leq 111\text{ °C}$	-	5			A
$I_{T(RMS)}$	RMS on-state current	all conduction angles	-	8			A
$I_{TSM}$	Non-repetitive peak on-state current	half sine wave; $T_j = 25\text{ °C}$ prior to surge $t = 10\text{ ms}$	-	75			A
$I^2t$	$I^2t$ for fusing	$t = 8.3\text{ ms}$	-	82			A
$di_T/dt$	Repetitive rate of rise of on-state current after triggering	$t = 10\text{ ms}$ $I_{TM} = 10\text{ A}$ ; $I_G = 50\text{ mA}$ ; $di_G/dt = 50\text{ mA}/\mu\text{s}$	-	28			A <sup>2</sup> s
$I_{GM}$	Peak gate current		-	50			A/ $\mu\text{s}$
$V_{RGM}$	Peak reverse gate voltage		-	2			A
$P_{GM}$	Peak gate power		-	5			V
$P_{G(AV)}$	Average gate power	over any 20 ms period	-	5			W
$T_{stg}$	Storage temperature		-40	0.5			W
$T_j$	Operating junction temperature		-	150			°C
				125 <sup>2</sup>			°C

1 Although not recommended, off-state voltages up to 800V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15 A/ $\mu\text{s}$ .

2 Note: Operation above 110°C may require the use of a gate to cathode resistor of 1k $\Omega$  or less.

# Thyristors logic level

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### THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Thermal resistance junction to mounting base	in free air	-	-	2.0	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient		-	60	-	K/W

### STATIC CHARACTERISTICS

$T_j = 25\text{ °C}$  unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{GT}$	Gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$	-	50	200	$\mu\text{A}$
$I_L$	Latching current	$V_D = 12\text{ V}$ ; $I_{GT} = 0.1\text{ A}$	-	0.4	10	mA
$I_H$	Holding current	$V_D = 12\text{ V}$ ; $I_{GT} = 0.1\text{ A}$	-	0.3	6	mA
$V_T$	On-state voltage	$I_T = 16\text{ A}$	-	1.3	1.6	V
$V_{GT}$	Gate trigger voltage	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$	-	0.4	1.5	V
$I_D, I_R$	Off-state leakage current	$V_D = V_{DRM(max)}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 110\text{ °C}$	0.1	0.2	-	V
		$V_D = V_{DRM(max)}$ ; $V_R = V_{RRM(max)}$ ; $T_j = 125\text{ °C}$	-	0.1	0.5	mA

### DYNAMIC CHARACTERISTICS

$T_j = 25\text{ °C}$  unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$dV_D/dt$	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM(max)}$ ; $T_j = 125\text{ °C}$ ; exponential waveform; $R_{GK} = 100\ \Omega$	50	100	-	V/ $\mu\text{s}$
$t_{gt}$	Gate controlled turn-on time	$I_{TM} = 10\text{ A}$ ; $V_D = V_{DRM(max)}$ ; $I_G = 5\text{ mA}$ ; $dI_G/dt = 0.2\text{ A}/\mu\text{s}$	-	2	-	$\mu\text{s}$
$t_q$	Circuit commutated turn-off time	$V_D = 67\% V_{DRM(max)}$ ; $T_j = 125\text{ °C}$ ; $I_{TM} = 12\text{ A}$ ; $V_R = 24\text{ V}$ ; $dI_{TM}/dt = 10\text{ A}/\mu\text{s}$ ; $dV_D/dt = 2\text{ V}/\mu\text{s}$ ; $R_{GK} = 1\text{ k}\Omega$	-	100	-	$\mu\text{s}$

# Thyristors logic level

## BT258 series

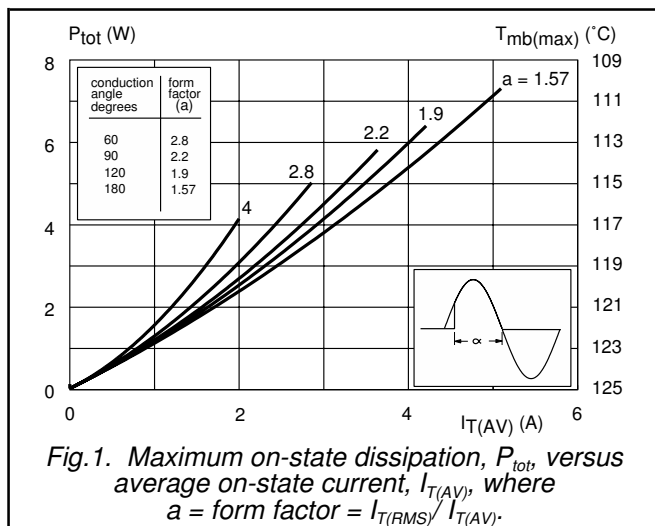


Fig.1. Maximum on-state dissipation,  $P_{tot}$ , versus average on-state current,  $I_{T(AV)}$ , where  $a = \text{form factor} = I_{T(RMS)}/I_{T(AV)}$ .

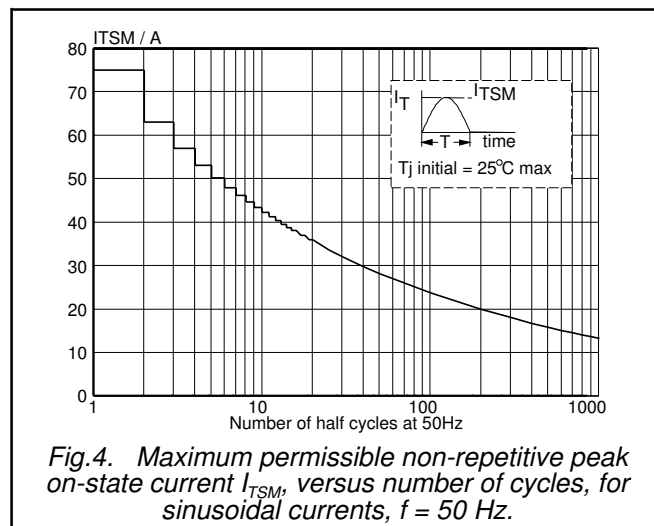


Fig.4. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus number of cycles, for sinusoidal currents,  $f = 50$  Hz.

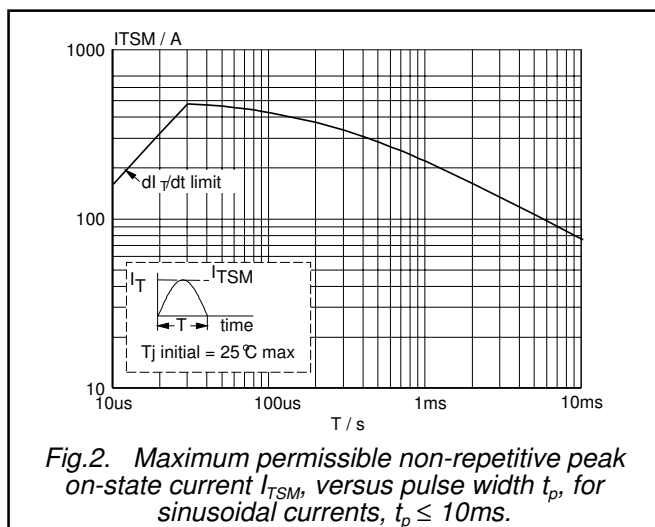


Fig.2. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus pulse width  $t_p$ , for sinusoidal currents,  $t_p \leq 10$  ms.

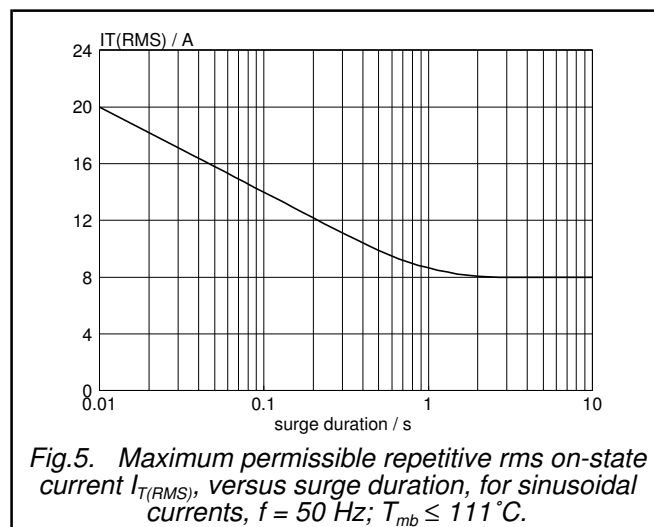


Fig.5. Maximum permissible repetitive rms on-state current  $I_{T(RMS)}$ , versus surge duration, for sinusoidal currents,  $f = 50$  Hz;  $T_{mb} \leq 111^\circ\text{C}$ .

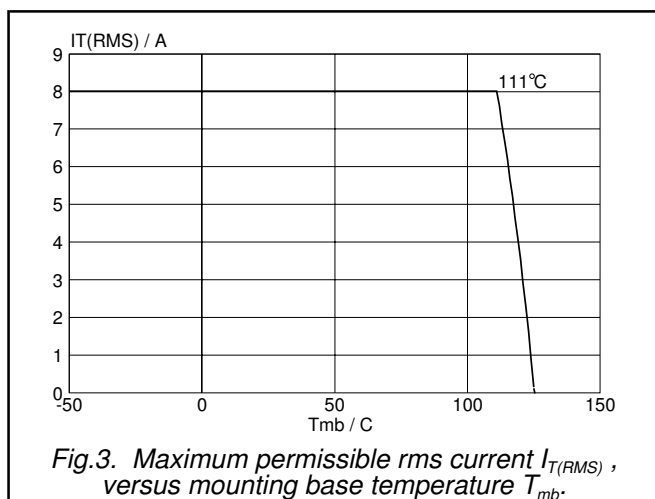


Fig.3. Maximum permissible rms current  $I_{T(RMS)}$ , versus mounting base temperature  $T_{mb}$ .

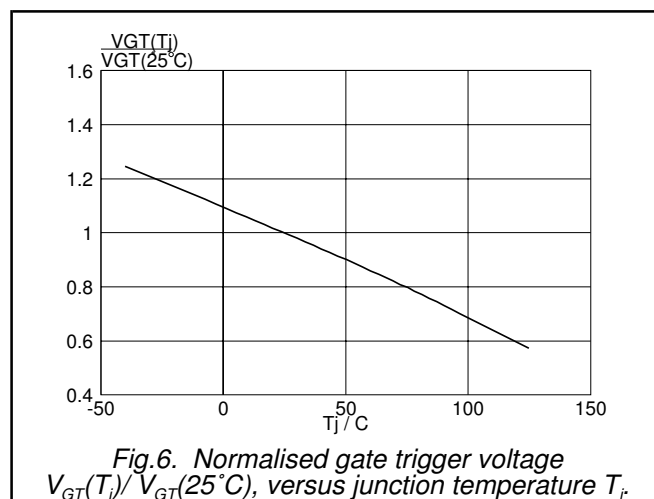
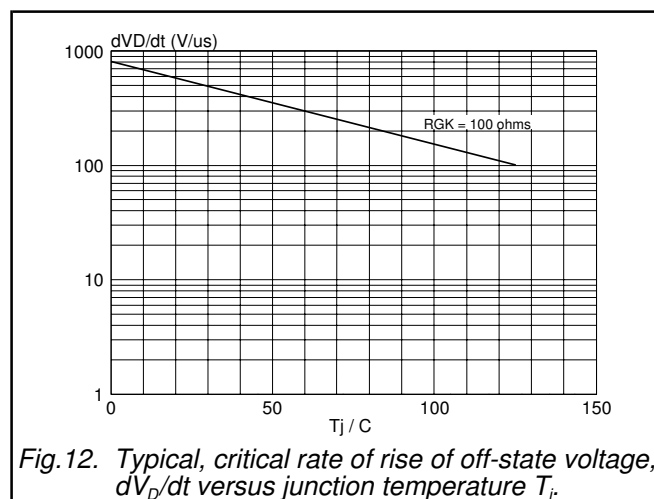
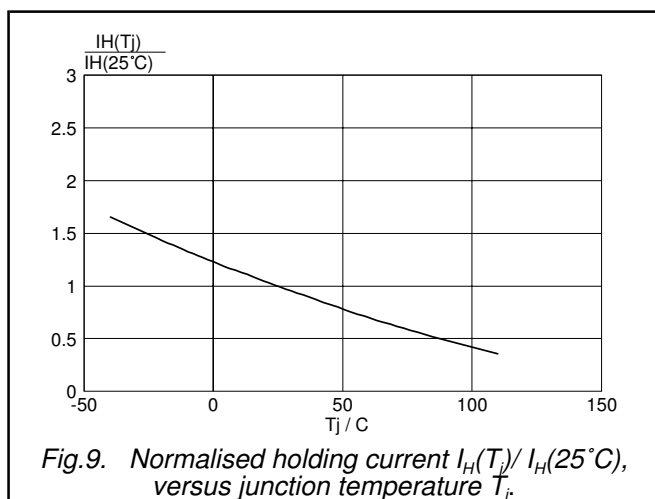
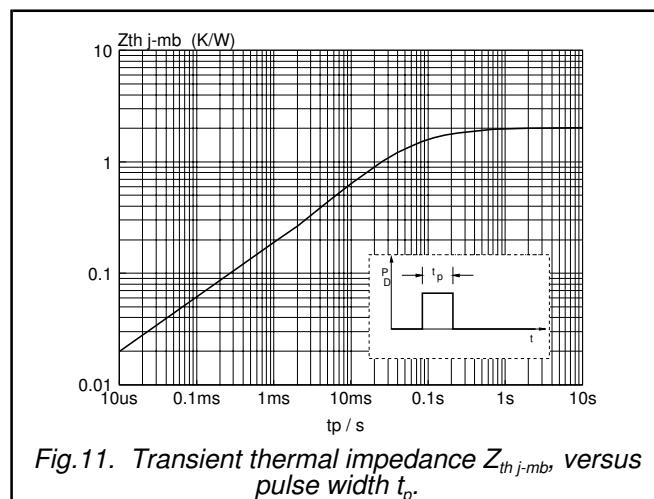
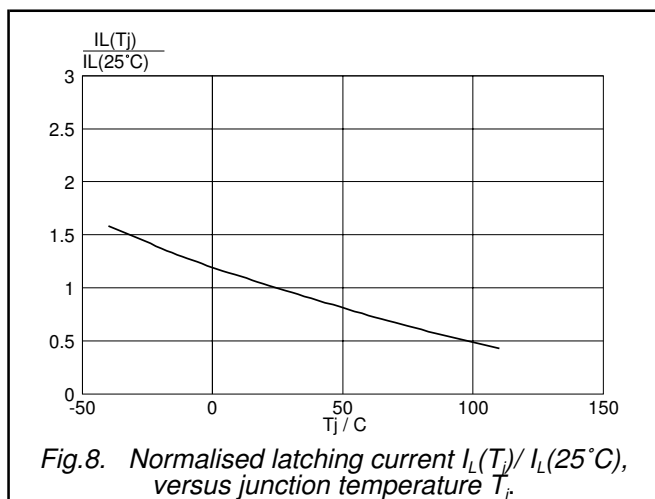
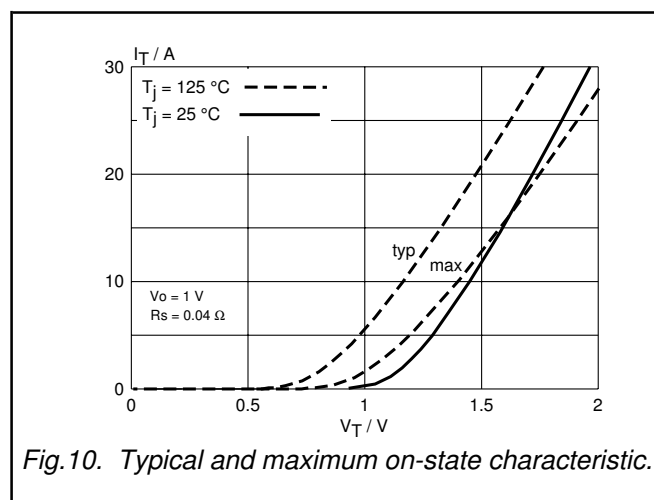
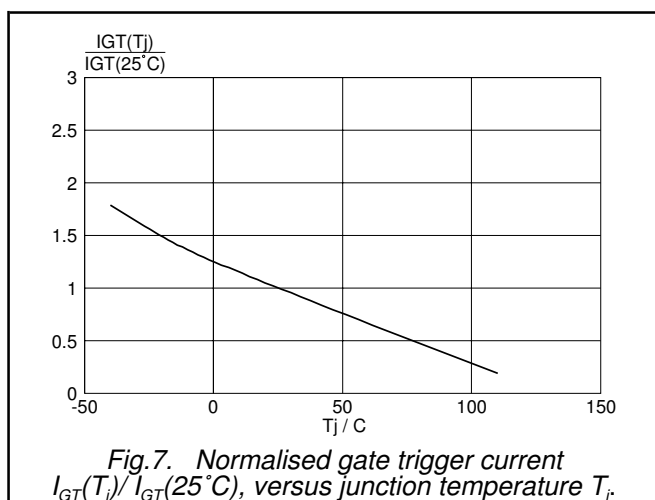


Fig.6. Normalised gate trigger voltage  $V_{GT}(T_j)/V_{GT}(25^\circ\text{C})$ , versus junction temperature  $T_j$ .

# Thyristors logic level

## BT258 series



# Thyristors logic level

## BT258 series

### MECHANICAL DATA

Dimensions in mm

Net Mass: 2 g

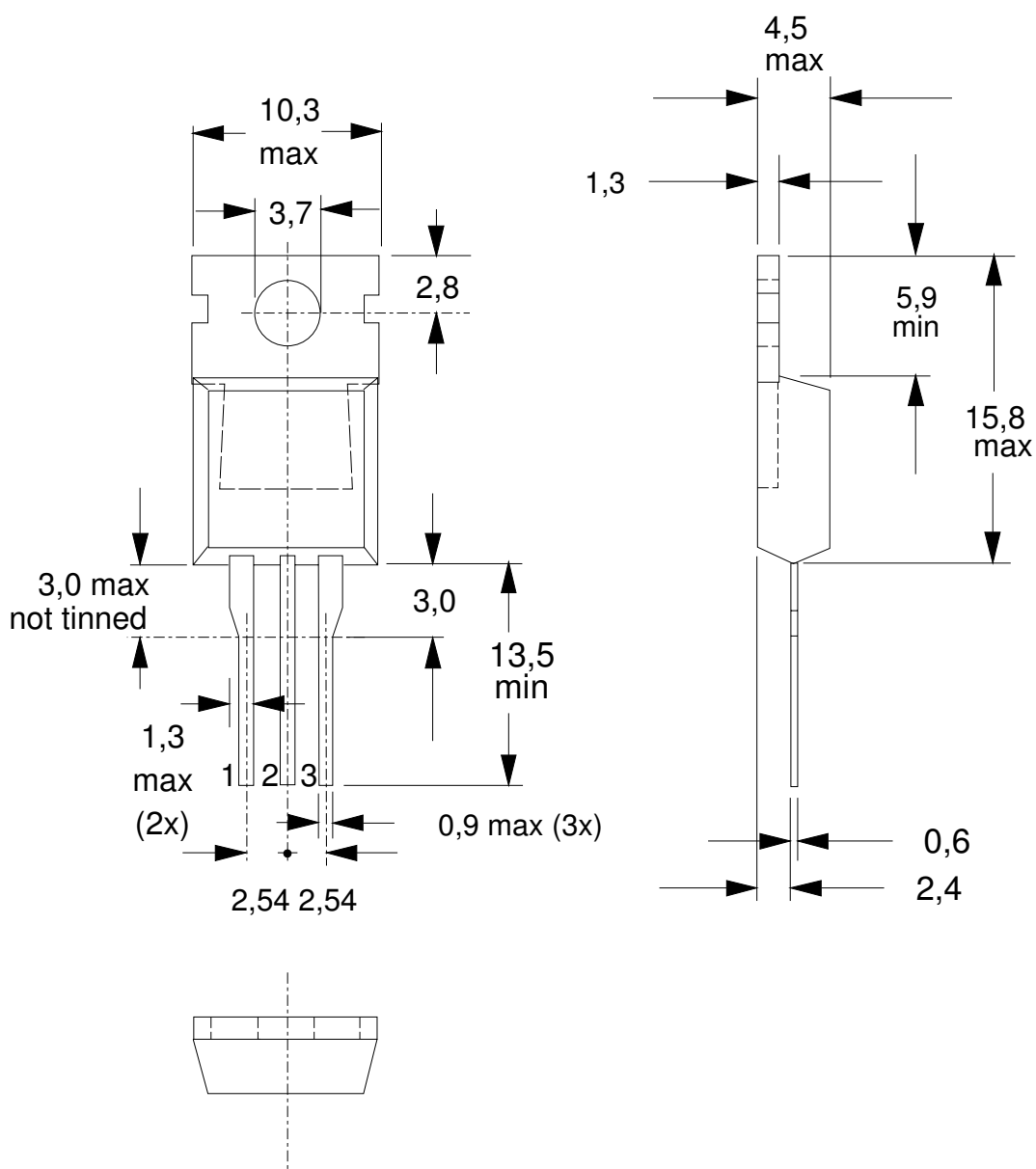


Fig.13. SOT78 (TO220AB). pin 2 connected to mounting base.

#### Notes

1. Refer to mounting instructions for SOT78 (TO220) envelopes.
2. Epoxy meets UL94 V0 at 1/8".

## Legal information

### DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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